

Novel Materials for Renewable Energy Applications : EFREE II

Overview November 12, 2014 P Craig Taylor









- Synthesis Laboratory (nanoparticle capabilities)
- Clean Room (class 1000)
- Processing Laboratory (class 10,000)
- PECVD Laboratory
- Characterization Laboratory (optical, electronic, defect characterization)

Characterization Techniques



- Photothermal deflection spectroscopy
- Electron paramagnetic resonance
- Photoluminescence (PL)
- PL excitation spectroscopy
- Solar simulator (for PV cell testing)
- Optical absorption spectroscopy
- Raman spectroscopy
- Electron microscopy
- Many other techniques

Photothermal Deflection Spectroscopy (PDS)



Optical Absorption in a Nanocrystalline/Amorphous Si Composite



- 50 % volume fraction of ~6 X 20 nm nanocrystals
- Higher absorption at longer wavelengths in nc-Si:H
- No sharp drop-off of absorption in nc-Si:H

Electron Paramagnetic Resonance



Comparison of LESR in *a*-Si:H and nc-Si:H



- CW YAG laser
- T = 7 K
- nc-Si:H: g ≈ 1.998
 a-Si:H: g ≈ 2.005

Same Signal Also Seen with Ar+ Laser





30 years ago: Two forms of crystalline carbon Now: An explosive growth in applications of carbon allotropes

Si is poised to undergo a similar transformation

Could drive the next 50 years of Si micro- and optoelectronics



- Direct band gaps and high extinction coefficients theoretically predicted
- Tunable band gaps covering important 1.5-2.5eV range
- "Stable" at temperatures appropriate for optoelectronic devices
- Novel synthesis to form macroscopic quantities of metestable phases demonstrated: Colloidal synthesis of high pressure BC8 phase, Solid state formation of clathrates



Direct Band Gap Silicon Allotropes

Qianqian Wang,^{†,⊥} Bo Xu,^{†,⊥} Jian Sun,^{§,⊥} Hanyu Liu,[‡] Zhisheng Zhao,[∥] Dongli Yu,[†] Changzeng Fan,[†] and Julong He^{*,†}

[†]State Key Laboratory of Metastable Materials Science and Technology, Yanshan University, Qinhuangdao 066004, Hebei Province, China

[§]Department of Physics and National Laboratory of Solid State Microstructures, Nanjing University, Nanjing 210093, China

[‡]Department of Physics and Engineering Physics, University of Saskatchewan, Saskatchewan, Canada, S7N 5E2

^{II}Geophysical Laboratory, Carnegie Institution of Washington, Washington, DC 20015, United States



Figure 1. Crystal structures of (a) oC12-Si, (b) tP16-Si, (c) oF16-Si, (d) tI16-Si, (e) hP12-Si, and (f) mC12-Si.



Characterization of Optical and Electronic Properties



- BC8 Si
- Si₂₄
- Clathrate Si
- Nanocrystalline Si
 - Self standing
 - In amorphous matrices
- Alloys with C, Ge ...
- Other structures
 - Carbon-based nano- and meso-materials





Clathrate Si



Transfer of basic discoveries



• Clathrates for Renewable Energy Applications



Seeds Spawn New Transformative Programs





Walsh, M. R.; Koh, C. A.; Sloan, E. D.; Sum, A. K.; Wu, D. T., "Microsecond Simulation of Spontaneous Methane Hydrate Nucleation and Growth" *Science*, **2009**, 326 (5956), 1095-1098.

Seeds Spawn New Transformative Programs



Molecular Hydrogen Stored in Clathrate Si

- Structure nucleates around Na atoms
- Storage is reversible

Video courtesy of Mark Lusk



Background



Clathrate frameworks are built from covalently bound cages connected in 3D. Guest ions (green spheres) reside within the void space in these cages. Arrows indicate guest-guest and guest-host interactions & guest mobility



Theoretical Component



Top: MD simulations can reveal the transformation mechanism from amorphous (upper layer) to clathrate (lower layer) structures. *Bottom:* Si_{136} clathrate thin film grown on sapphire.



Na removal



Experimental Na guest removal by sublimation and etching, indicating Na motion is facile in the Si_{136} framework.



Synthesis and optical band gaps of alloyed Si–Ge type II clathrates⁺

Lauryn L. Baranowski, Lakshmi Krishna, Aaron D. Martinez, Taufik Raharjo, Vladan Stevanović, Adele C. Tamboli and Eric S. Toberer*

Growing and characterizing the clathrate form of silicon has tremendous potential to dramatically transform microelectronics and opto-electronics in the 21st century

Colloidal Synthesis of an Exotic Phase of Silicon: The BC8 Structure

Shreyashi Ganguly, Nasrin Kazem, Danielle Carter, and Susan M. Kauzlarich*

Department of Chemistry, University of California, Davis, California 95616, United States

Supporting Information

Nanocrystalline Si

Nanocrystalline Si

Nanocrystalline Si (2-4 nm diameter) being removed from the reactor.

Hot Carrier Transfer: Conventional nc-Si:H

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1.0

Science and Engineering Center

Objective

"Engineered" Nanocrystalline Si that takes advantage of hot carrier transfer to:

- Tune band gap through crystallite size and amorphous matrix properties
- Increase photostability
- Improve doping efficiency
- Improve mobility
- Achieve single junction efficiencies and stability not possible with conventional "thin film Si"
- Create high efficiency, stable, SiNPbased multijunction cells
- Explore the potential for true hot carrier architectures that exceed the Shockley-Queisser limit

An integrated theoretical and experimental approach

Plasma Synthesized Si Quantum Dots

Goal - Si quantum dots with:

- Control of dot size
- Narrow size distribution
- Controlled surface properties
- Mechanisms for assembly into films
- High throughput synthesis

Our approach: Si nanoparticle growth by continuous-flow PECVD

- Dilute SiH₄/Ar plasma
- Highly exothermic surface reactions heat particles – nucleation and growth of crystalline Si
- Collect downstream
- Passivate and assemble in colloidal phase or
- Gas-phase processing downstream; embed in matrix

Sequential and Concurrent Deposition

Crystal fraction:

- Sequential growth controlled by varying the deposition times of each layer
- Concurrent growth P_2 (PECVD) controls the exit velocity of the SiNPs and therefore the crystalline fraction

Absorption spectrum and PL of SF₆ treated isolated Si nanoparticles

ESR of Oxidized SF6 Treated SiNPs

SF6 treated SiNPs and Hybrid Structure with Structu

Si nanowires

Sn Seeded, PECVD Grown Si Nanowires

Vapor-Liquid-Solid growth by CVD

- Au is the most common catalyst
- Growth temperatures 600-900°C

Sn Seeds

- Sn isovalent
- Eutectic T = 232° C (Au: 363° C)
- Si solubility < 10⁻⁴ (Au: 18%)

PECVD

- a-Si:H and nc-Si
- Lower processing temperatures
- Sn seeds formed by H₂ plasma reduction of SnO₂ coated glass

PECVD and/or Sn seeds not extensively studied

Membranes

Macroscopic effect of nano sized particles

Super ionic hybrids Pd nano particles in BCY20

Tungsten oxide nanoparticles and nanorods in 3M ionomer

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Significance: Incorporation of appropriate nano particles in both high/low temperature ion conductors significantly enhances protonic conductivity

Sun Edison/EXCEL Facility Alamosa, CO

Backup Slides

